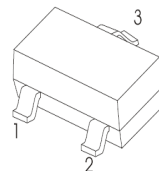


**SOT-23 Plastic-Encapsulate Transistors****MMBTA64** TRANSISTOR (PNP)**FEATURES**

- For Applications Requiring High Current Gain

MARKING:2V**MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)**

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current	-800	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	$^{\circ}\text{C/W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

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1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-10			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{V}$, $I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-10\text{V}$, $I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-5\text{V}$, $I_C=-10\text{mA}$	10			K
	$h_{FE(2)}^*$	$V_{CE}=-5\text{V}$, $I_C=-100\text{mA}$	20			K
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-100\text{mA}$, $I_B=-0.1\text{mA}$			-1.5	V
Base-emitter voltage	V_{BE}^*	$V_{CE}=-5\text{V}$, $I_C=-100\text{mA}$			-2	V
Transition frequency	f_T	$V_{CE}=-5\text{V}$, $I_C=-10\text{mA}$, $f=100\text{MHz}$	125			MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycles $\leq 2.0\%$.